

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	I <sub>C</sub>	200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

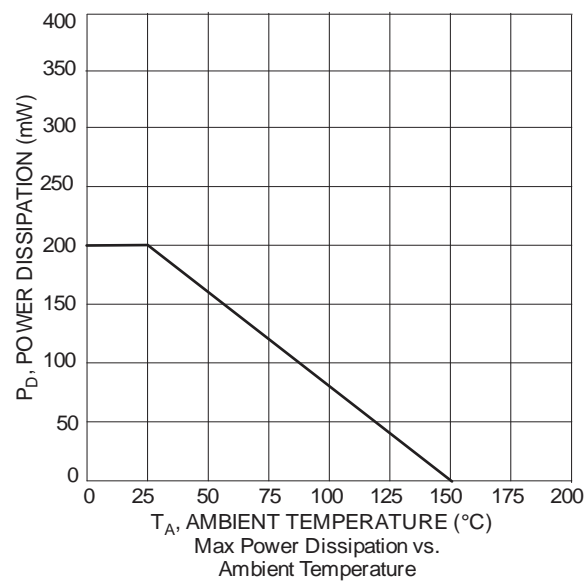
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## Thermal Characteristics and Derating Information

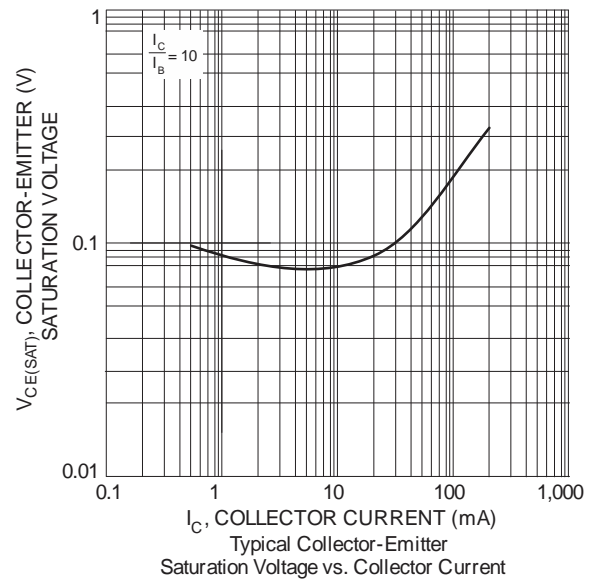
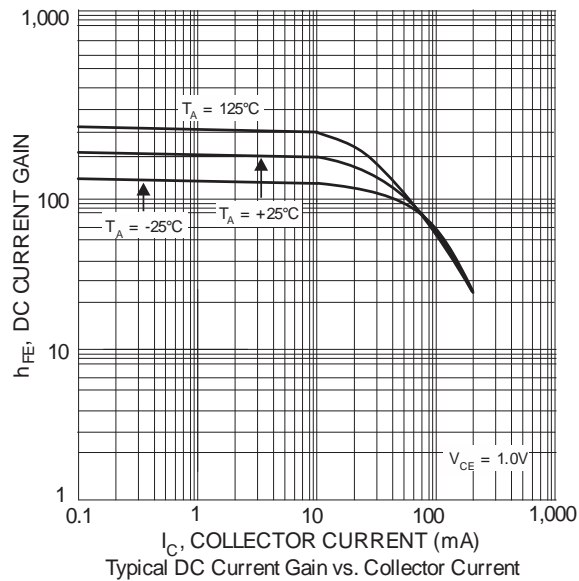
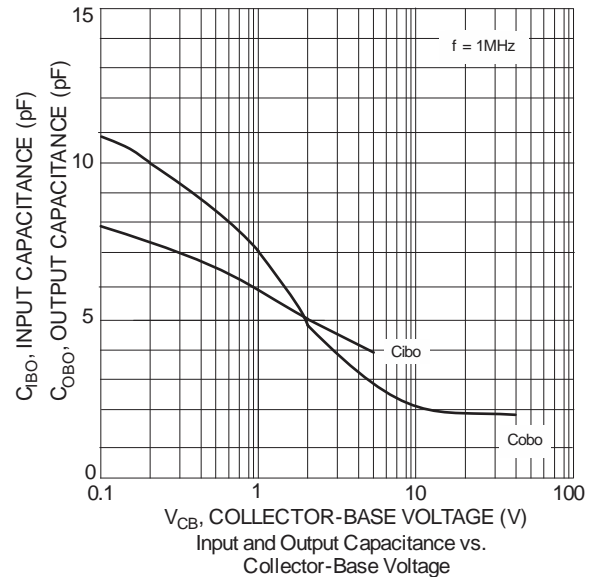
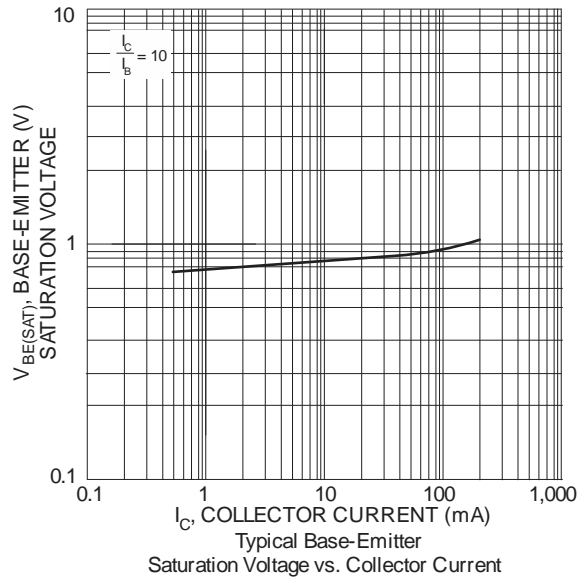


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	—	V	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40	—	V	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	—	V	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3V
Base Cutoff Current	I <sub>BL</sub>	—	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3V
<b>ON CHARACTERISTICS (Note 8)</b>					
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	— — 300 — —	—	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 1V I <sub>C</sub> = 1mA, V <sub>CE</sub> = 1V I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1V I <sub>C</sub> = 50mA, V <sub>CE</sub> = 1V I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	0.25 0.30	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65 —	0.85 0.95	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	4	pF	V <sub>CB</sub> = 5V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	8	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	1	10	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1mA, f = 1.0MHz
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	100	400	—	
Output Admittance	h <sub>oe</sub>	1	40	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	—	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	—	5	dB	V <sub>CC</sub> = 5V, I <sub>C</sub> = 100μA, R <sub>S</sub> = 1kΩ, f = 1MHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>D</sub>	—	35	ns	V <sub>CC</sub> = 3V, I <sub>C</sub> = 10mA,
Rise Time	t <sub>R</sub>	—	35	ns	V <sub>BE(OFF)</sub> = -0.5V, I <sub>B1</sub> = 1mA

Notes: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

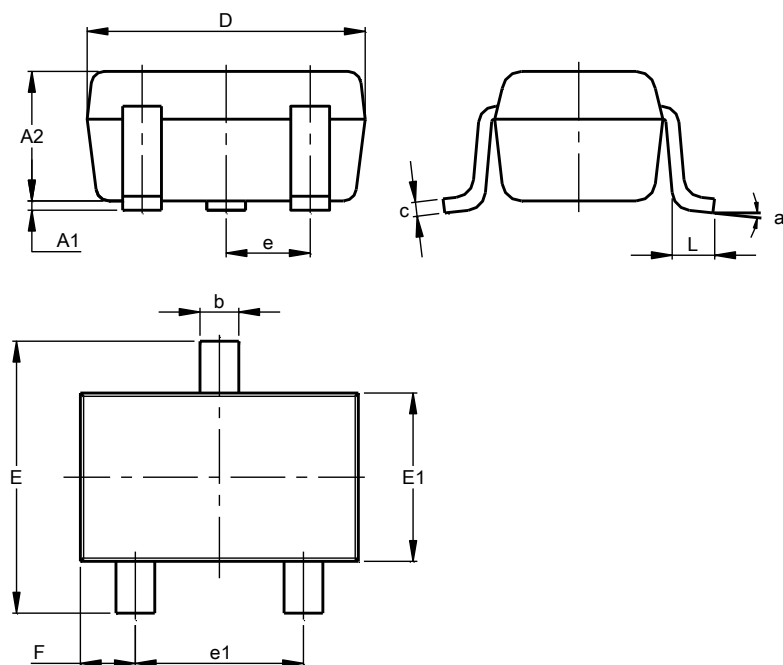
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT323

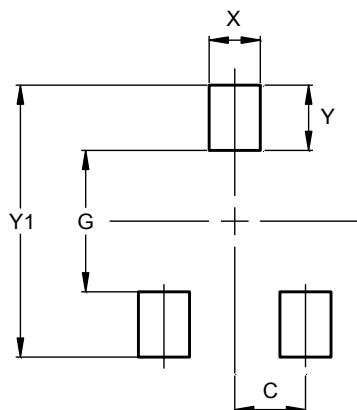


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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